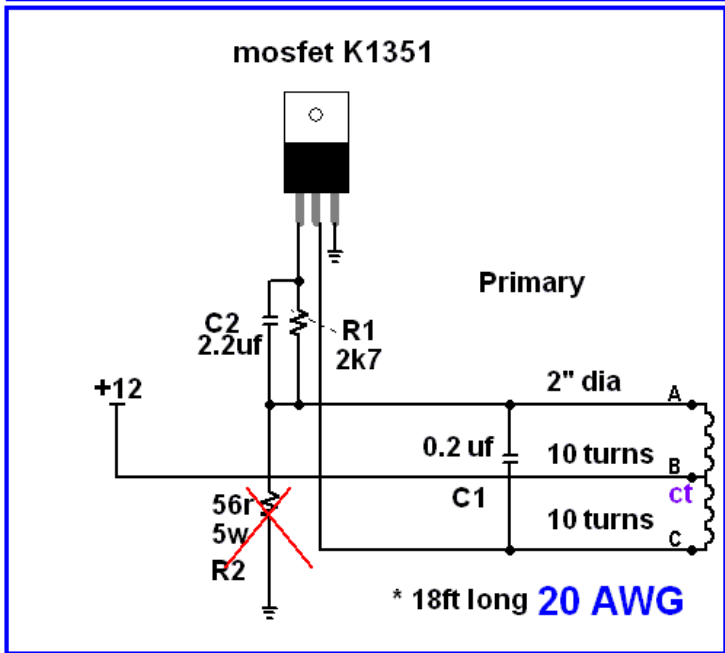
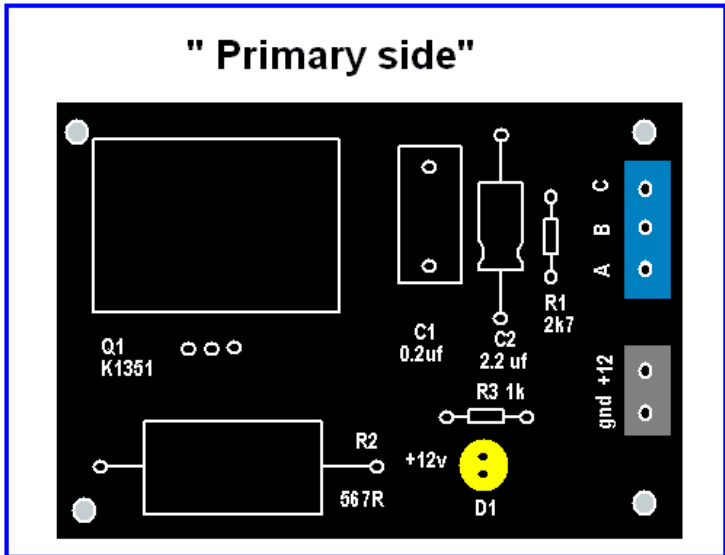
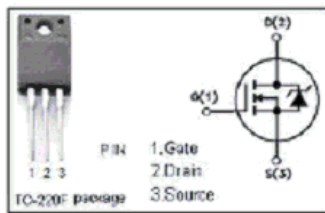
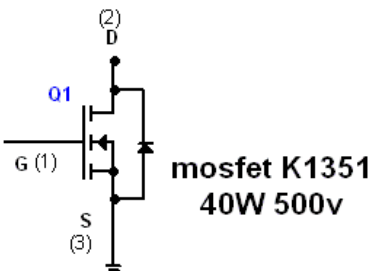
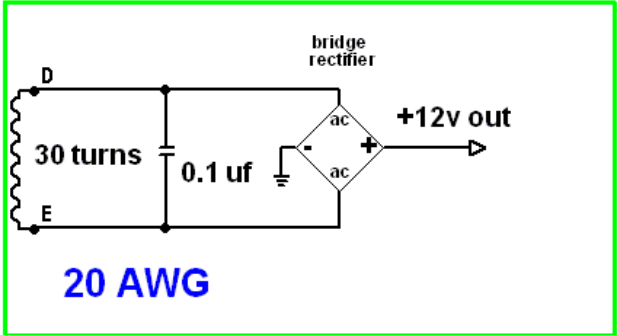


12v "wireless" power transformer



Secondary (Platter) spinner.



INCHANG SEMICONDUCTOR

isc N-Channel MOSFET Transistor

2SK1351

DESCRIPTION

- Drain Current $I_D=15A @ T_J=25^{\circ}C$
- Drain-Source Voltage: $V_{DS}=500V(Min)$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

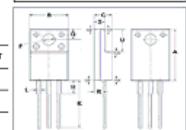
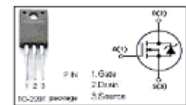
- Designed for high voltage, high speed power switching

ABSOLUTE MAXIMUM RATINGS($T_J=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage ($I_D=0$)	300	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current (continuous) @ $T_C=25^{\circ}C$	5	A
P_{tot}	Total Dissipation @ $T_C=25^{\circ}C$	40	W
T_J	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	$-55 \sim 150$	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{\theta J-C}$	Thermal Resistance, Junction to Case	3.125	$^{\circ}C/W$
$R_{\theta J-A}$	Thermal Resistance, Junction to Ambient	82.5	$^{\circ}C/W$



mm	
DR	10.65
DR	15.80
D	10.00
C	5.00
D	0.75
F	3.50
H	3.70
H	10.00
K	13.1
L	1.10
N	5.00
N	5.00
O	2.70
O	2.70
S	2.65
T	5.00